

## 1. General description

Planar passivated sensitive gate Silicon Controlled Rectifier in a SOT54 (TO-92) plastic package.

### 2. Features and benefits

- High voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate

## 3. Applications

- Earth leakage circuit breakers or Ground Fault Circuit Interrupters (GFCI)
- Ignition circuits
- Low power latching circuits
- Protection circuits / shut-down circuits: lighting ballasts
- · Protection circuits / shut-down circuits: Switched Mode Power Supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Mir	т Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	800	V
$I_{T(AV)}$	average on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 1</u>	-	-	0.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 2;</u> <u>Fig. 3</u>	-	-	0.8	A
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms	-	-	10	Α
		half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	-	9	А
Tj	junction temperature		-	-	125	°C
Static charact	eristics					,
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; $I_T$ = 10 mA; $T_j$ = 25 °C; Fig. 7	1	50	100	μΑ
Dynamic char	acteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; $R_{GK}$ = 1 kΩ; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	150	350	-	V/µs

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# **5. Pinning information**

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		А <del>- [-] -</del> К
2	G	gate		Ġ sym037
3	K	cathode	TO-92 (SOT54)	Symos

# 6. Ordering information

#### **Table 3. Ordering information**

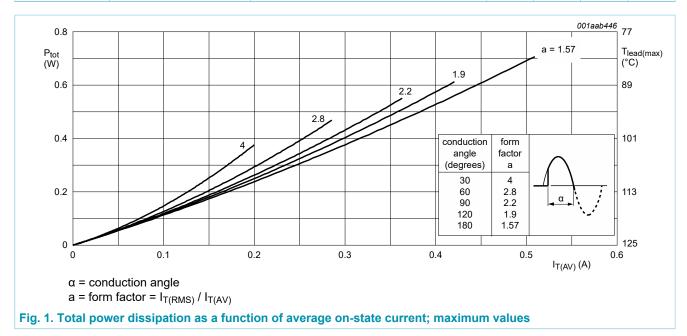
Type number	Package		
	Name	Description	Version
BT169H	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

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# 7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$V_{RRM}$	repetitive peak reverse voltage		-	800	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 1</u>	-	0.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on-	half sine wave; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 8.3  \text{ms}$	-	10	Α
	state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	9	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.41	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 2 \text{ A}$ ; $I_G = 10 \text{ mA}$ ; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$	-	50	A/µs
$I_{GM}$	peak gate current		-	1	Α
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C



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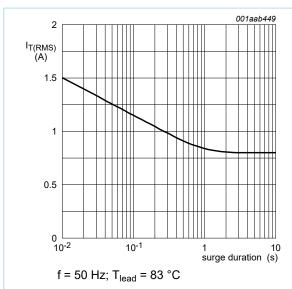


Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

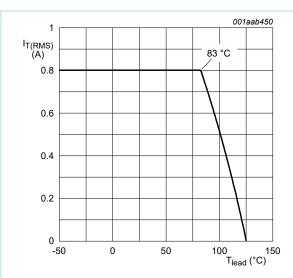


Fig. 3. RMS on-state current as a function of lead temperature; maximum values

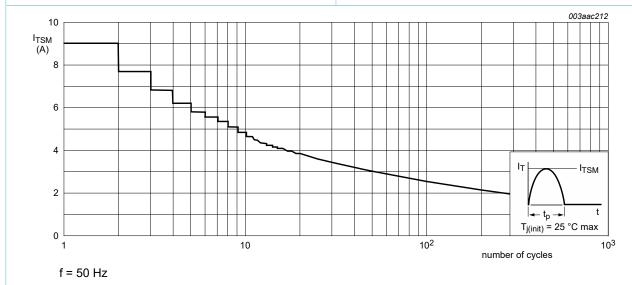
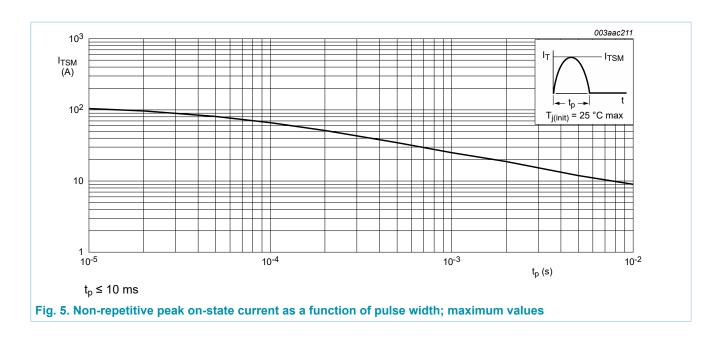


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	<u>Fig. 6</u>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

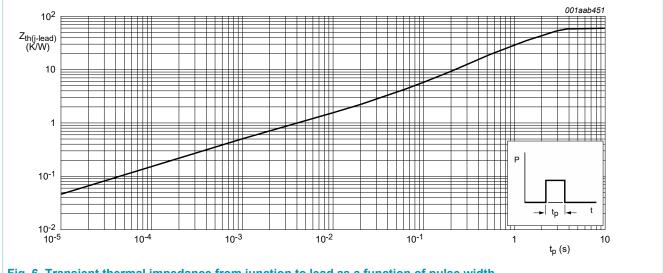


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

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### 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		1	'		,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 7	1	50	100	μA
IL	latching current	$V_D$ = 12 V; $I_G$ = 0.5 mA; $T_j$ = 25 °C; $R_{GK(ext)}$ = 1 k $\Omega$ ; Fig. 8	-	2	6	mA
l <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega;$ Fig. 9	-	1.5	3	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.2 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.25	1.7	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 11	-	0.5	0.8	V
		$V_D = 800 \text{ V}; I_T = 10 \text{ mA}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.3	0.5	-	V
I <sub>D</sub>	off-state current	$V_D = 800 \text{ V; } R_{GK(ext)} = 1 \text{ k}\Omega; T_j = 125 \text{ °C}$	-	0.05	0.1	mA
I <sub>R</sub>	reverse current	$V_R = 800 \text{ V}; T_j = 125 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
Dynamic cl	haracteristics			,		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; $R_{GK}$ = 1 k $\Omega$ ; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	150	350	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 2 A; $V_D$ = 800 V; $I_G$ = 10 mA; $dI_G/dt$ = 0.1 A/µs; $T_j$ = 25 °C	-	2	-	μs
t <sub>q</sub>	commutated turn-off time	$V_{DM}$ = 536 V; $T_j$ = 125 °C; $I_{TM}$ = 1.6 A; $V_R$ = 35 V; $(dI_T/dt)_M$ = 30 A/µs; $dV_D/dt$ = 2 V/µs; $R_{GK(ext)}$ = 1 k $\Omega$ ; $(V_{DM}$ = 67% of $V_{DRM})$	-	100	-	μs

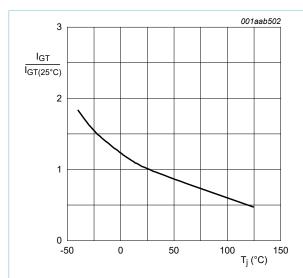


Fig. 7. Normalized gate trigger current as a function of junction temperature

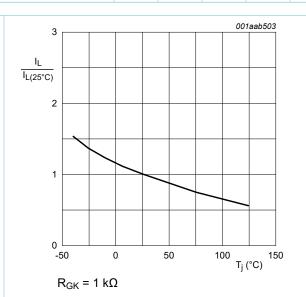


Fig. 8. Normalized latching current as a function of junction temperature

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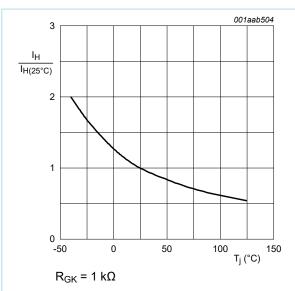


Fig. 9. Normalized holding current as a function of junction temperature

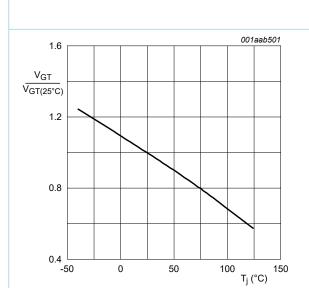
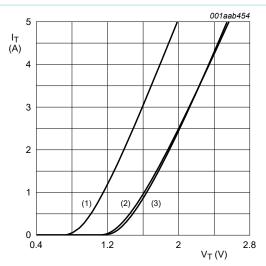


Fig. 11. Normalized gate trigger voltage as a function of junction temperature



 $V_o$  = 1.067 V;  $R_s$  = 0.187 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values (3)  $T_i$  = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

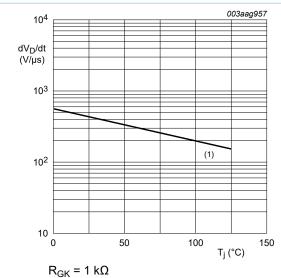


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

**BT169H** 

## 10. Package outline

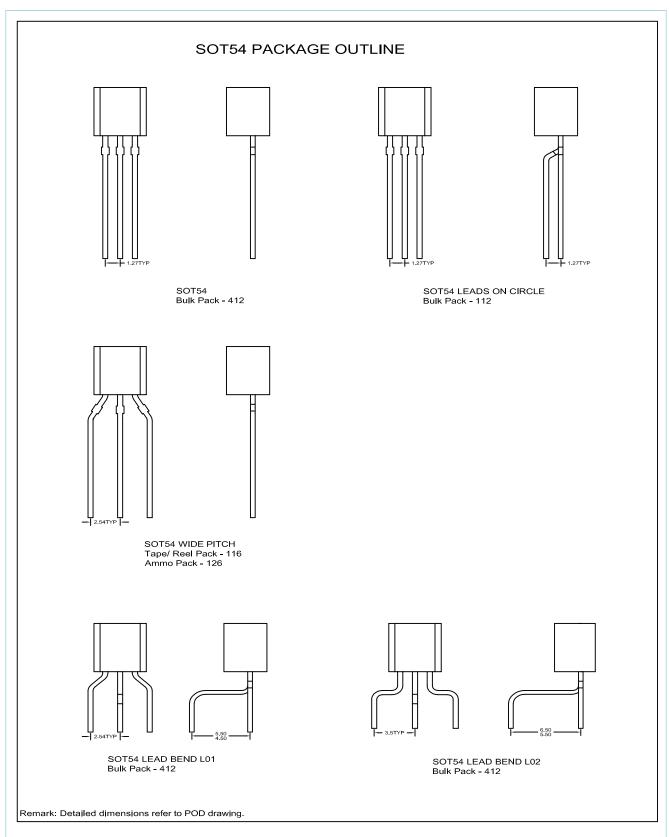


Fig. 13. Package outline TO-92 (SOT54)

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### 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
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Date of release: 5 September 2018

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